

# Synchrotron Radiation workshop

## e2v image sensors for high end applications

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# The e2v Group



**11** Global locations

**4** Production facilities

**50+** Countries served



**Founded in 1947**

**Annual sales of £225m**

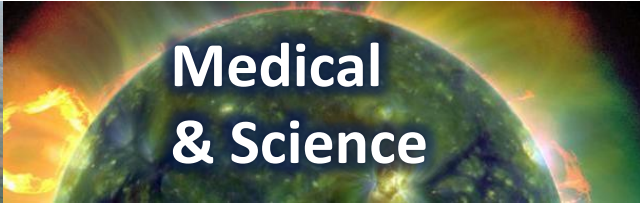
**1700 employees**

**500+ engineers & scientists**

**Operational facilities in Europe, the US and Asia**



**Aerospace  
& Defence**

A photograph of a dark-colored fighter jet in flight, banking to the left over a green and brown landscape.

**Medical  
& Science**

A composite image featuring a view of the Earth from space, showing the blue and green of the planet against the black of space and the orange and red of a sunset or sunrise.

**Commercial  
& Industrial**

A photograph of an industrial facility, possibly a refinery or chemical plant, with complex piping, metal structures, and a yellow safety railing in the foreground.

# Two Imaging Divisions

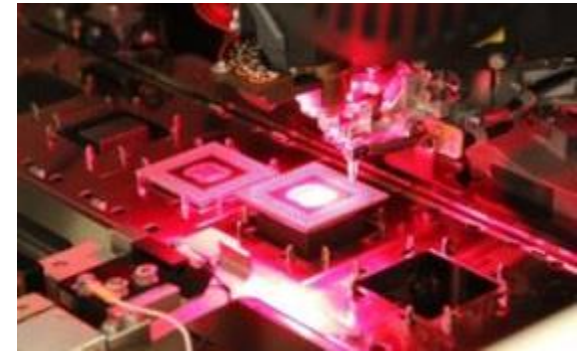
RF power



Imaging



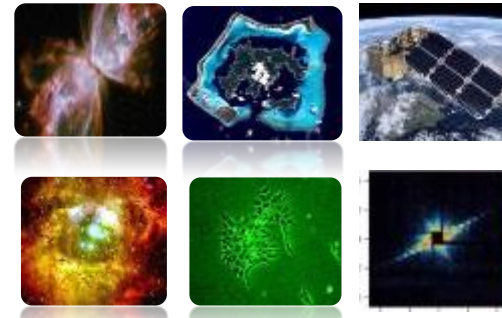
Semiconductors



Professional imaging



Space and physics imaging



# Topics

- e2v Introduction
- **Back-thinning summary**
- Examples of detector technology for space, science and astronomy:
- Synchrotron radiation detectors
- CCDs for XFELs
- CMOS sensors for synchrotron radiation detection

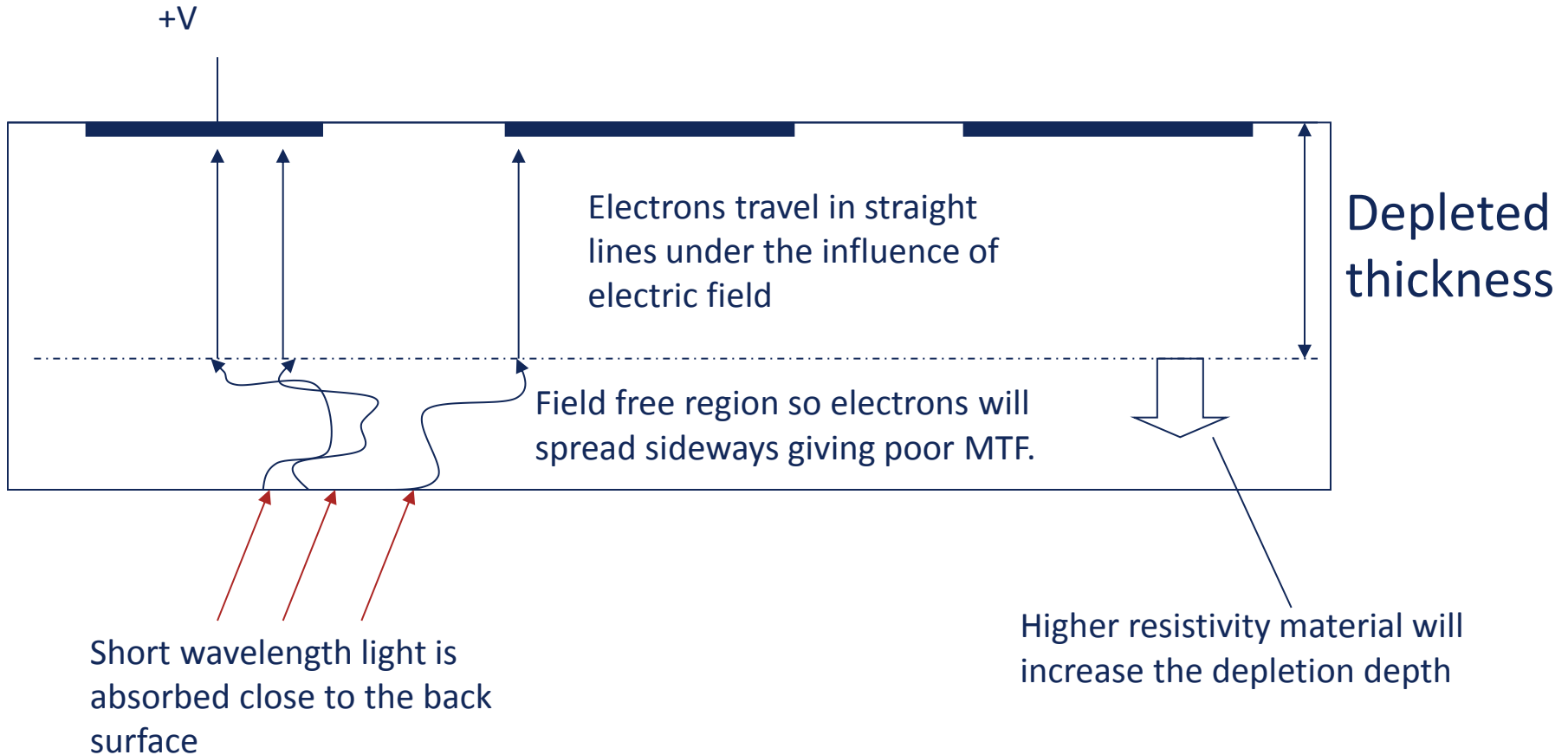
# Backthinning

**Quantum efficiency is critical for all of our applications – both for visible light and for extended spectral response to NIR or UV and soft x-rays**

**Standard devices have structure on the front that decreases this efficiency.**

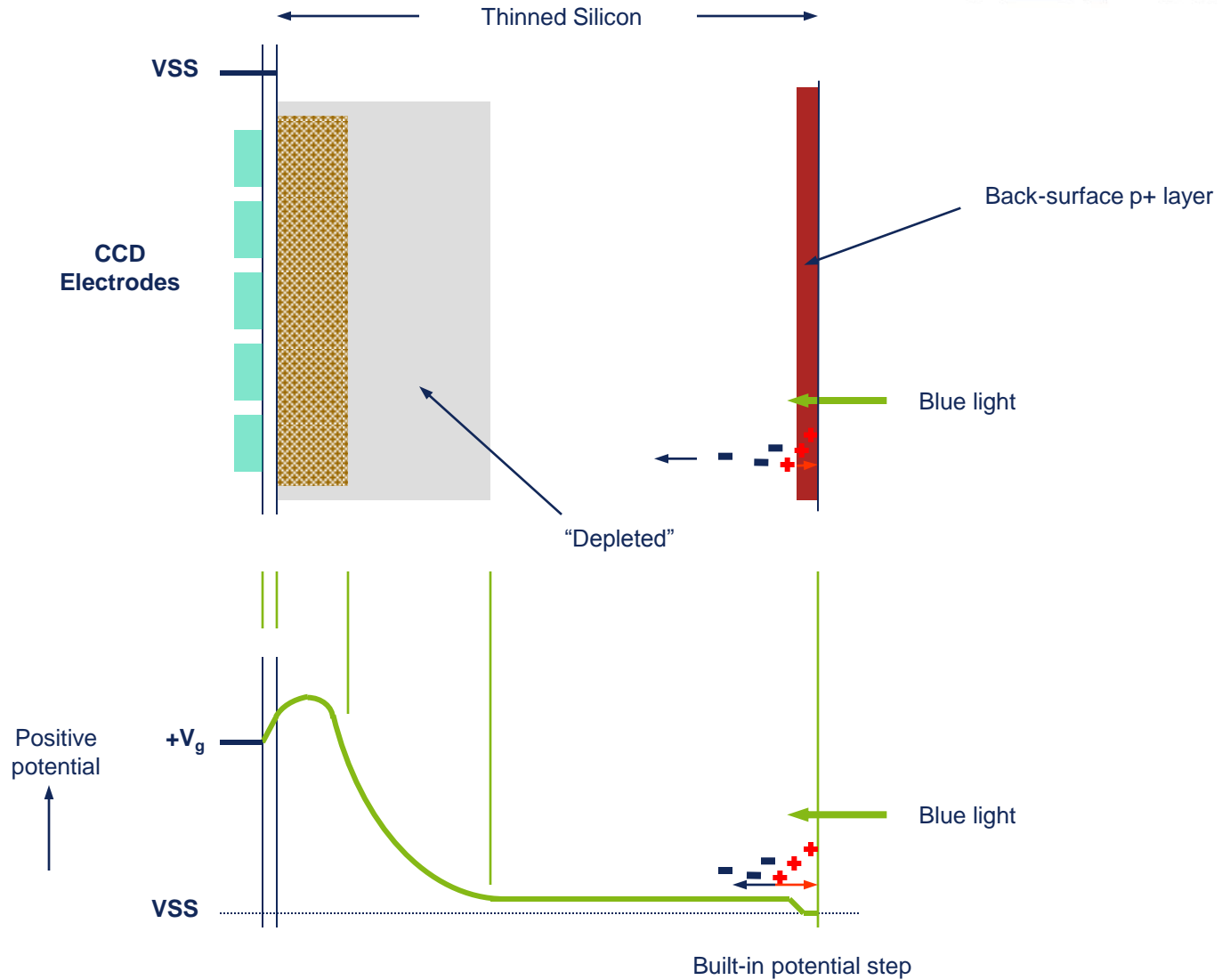
**To maximise spectral response backthinning has been used for many years for high end applications**

# Requirements for backthinning

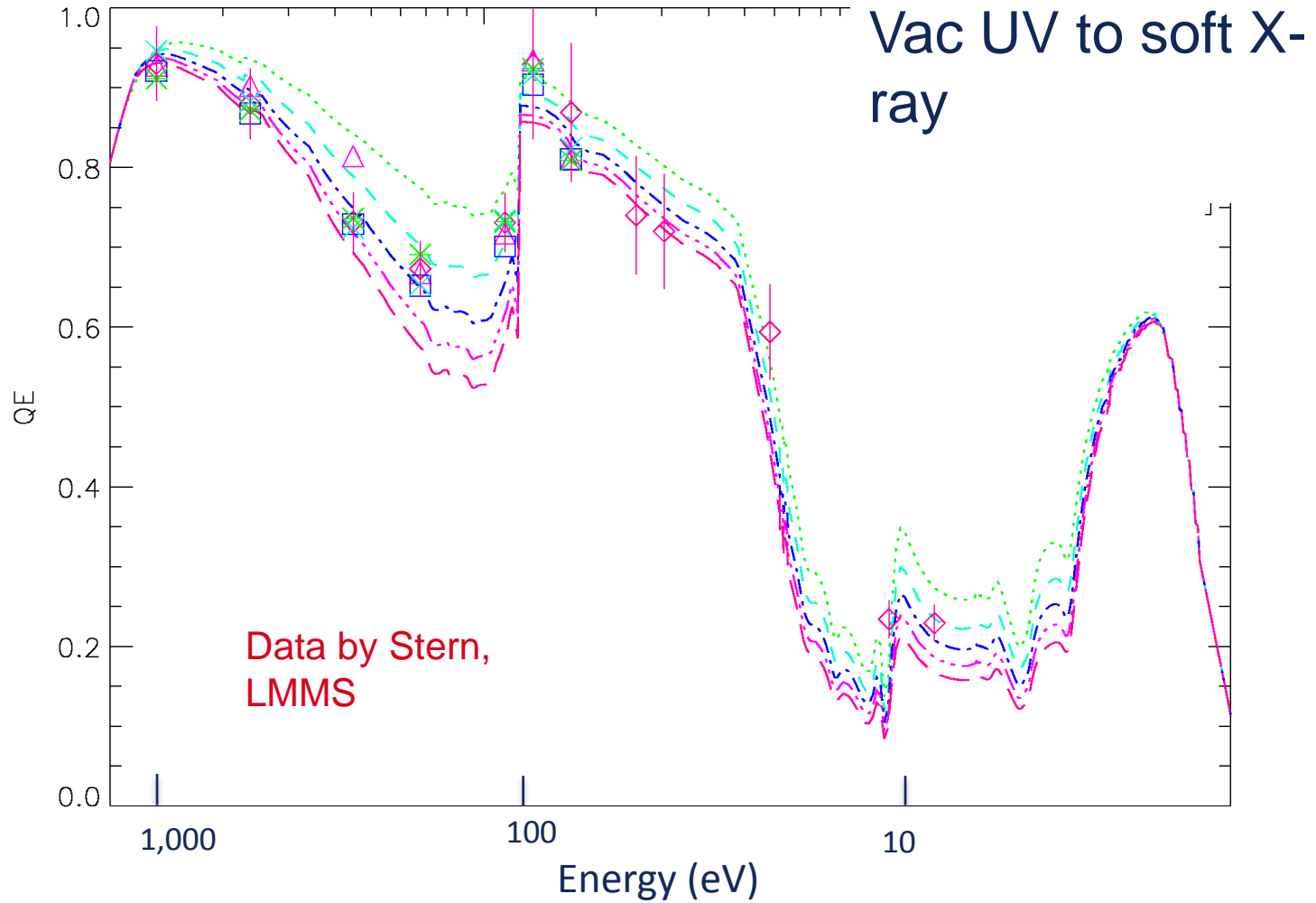


- MTF is determined by the ratio of the undepleted thickness to the pixel pitch
- Long wavelength QE is determined by the total thickness

# Back-thinned structure

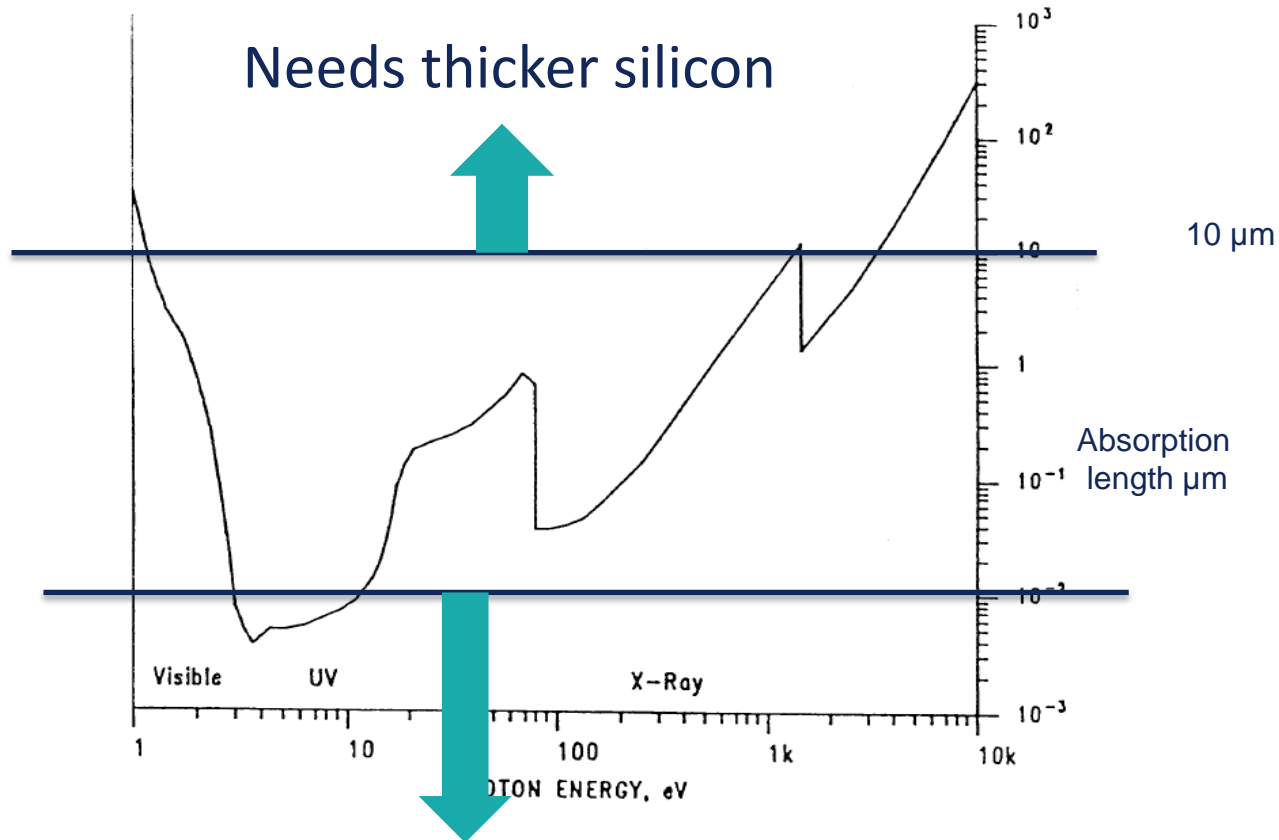


# Standard silicon QE





# Absorption length

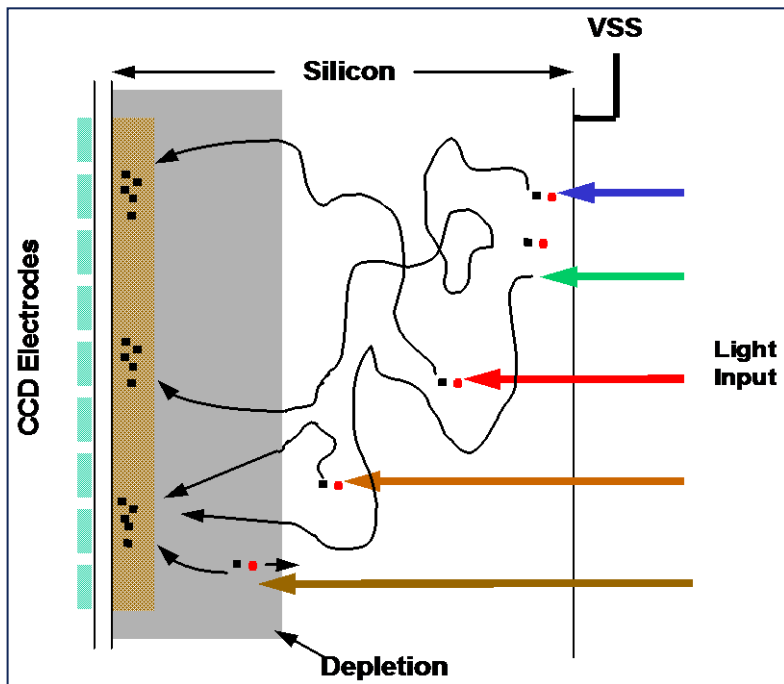


Back surface dead layer is critical

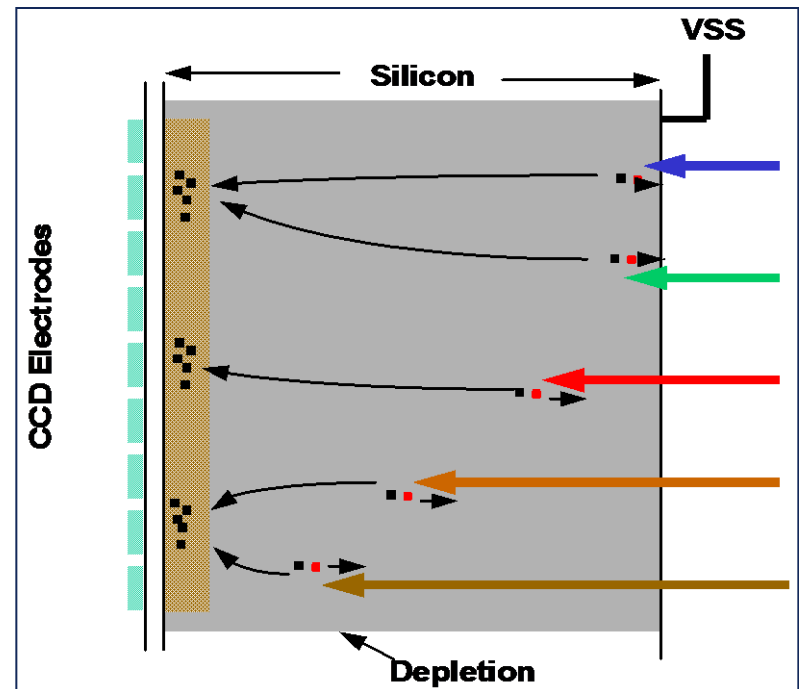
# HiRho CCDs

Full depletion (minimum undepleted depth) is necessary for high MTF (good PSF)

Thick bulk silicon is used with low doping density (high resistivity), and an increased substrate voltage  $V_{ss}$  (typically  $\sim -70V$ ) to extend the depth of depletion



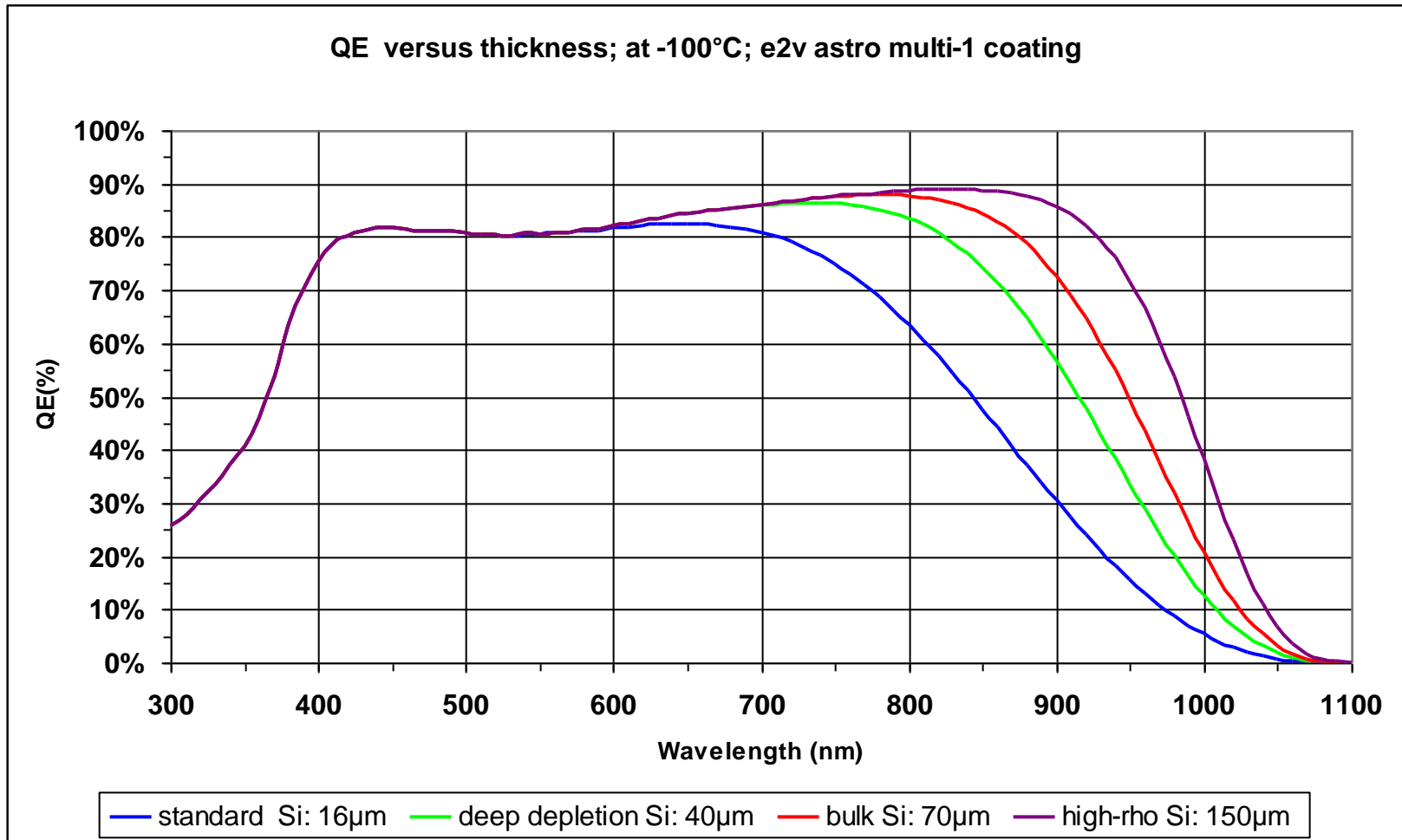
Low substrate voltage



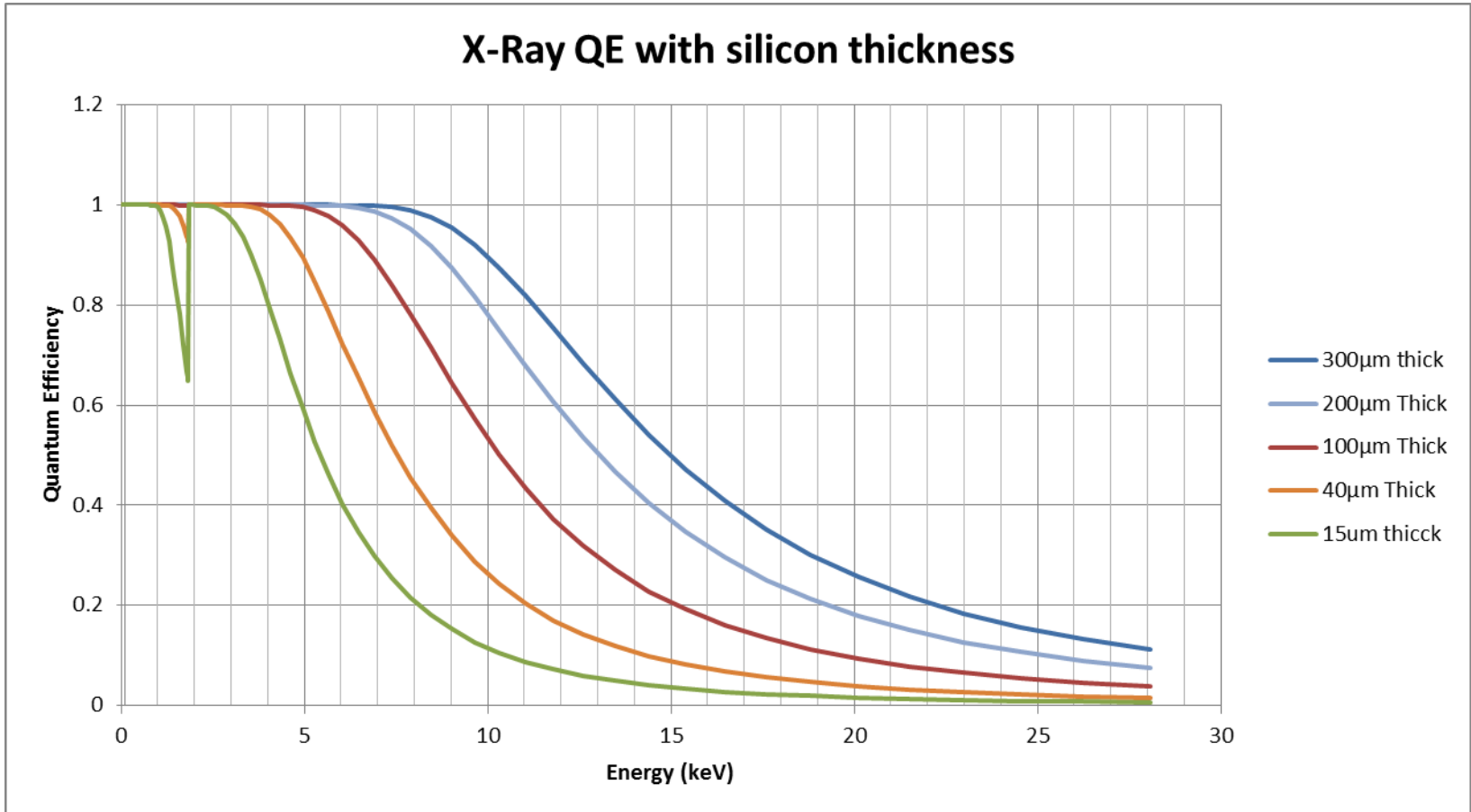
High substrate voltage

# Improving red response

- Modelled change in QE with device thickness is as shown below



# CCD Soft X-Ray QE



Variation of QE with silicon thickness – Model courtesy of Neil Murray, CEI, Open University, UK

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- **Examples of detector technology for space, science and astronomy:**
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- CCDs for XFELs
- CMOS sensors for synchrotron radiation detection

# Space – Earth Observation

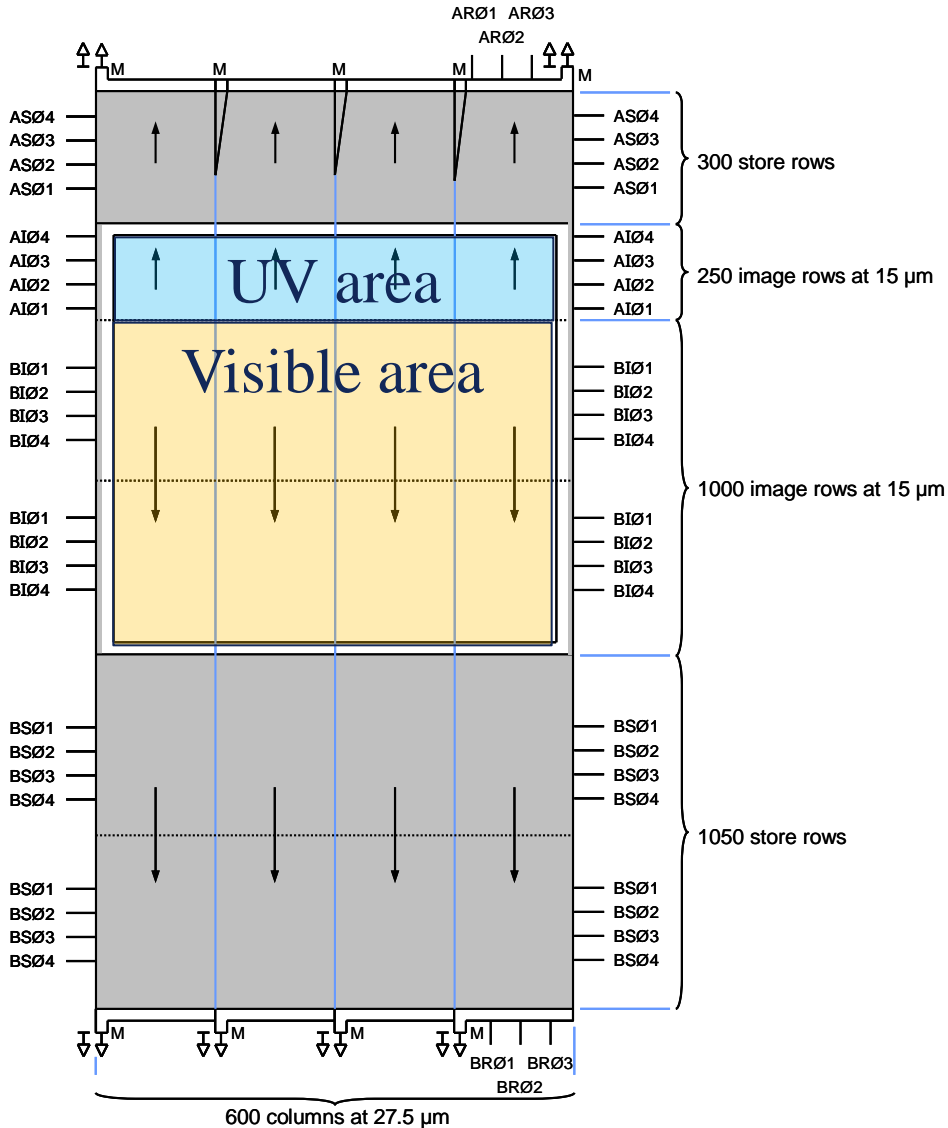
There are a number of existing and new hyperspectral programmes being run or currently in planning for ESA

- Sentinel 3
- Sentinel 4
- Tropomi
- Sentinel 5
- FLEX
- 3MI

The general trend with this devices is for larger pixel sizes and multiple readout ports to give higher speeds and increased peak signal (or dynamic range).

Most hyperspectral imagers still use CCDs but there is a trend towards CMOS as it allows higher frame rate and less crosstalk but at the expense of dynamic range

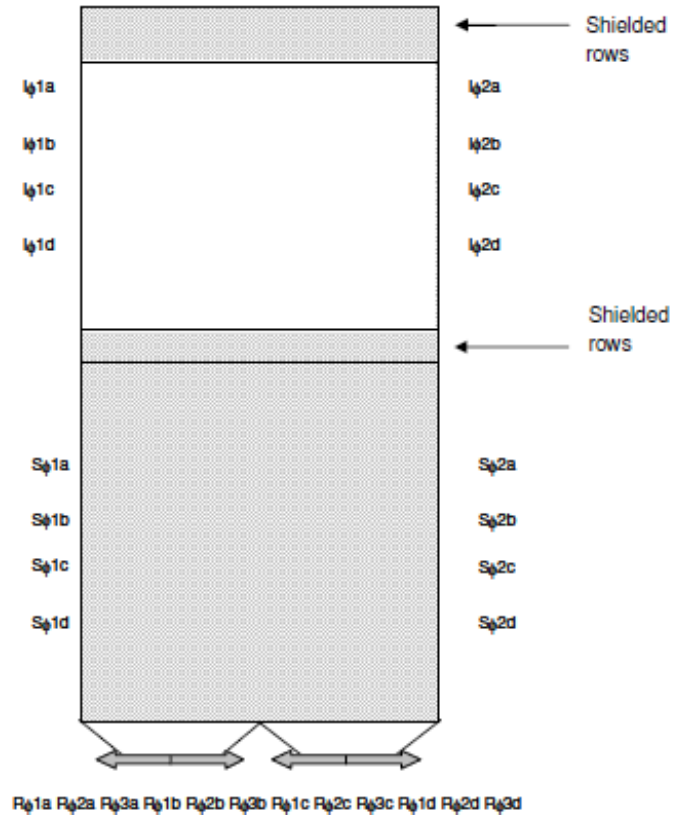
# Sentinel 4



- Readout speed is 1.2MHz with a noise of approximately 20e at 1.4µv/e (using real and dummy outputs for common mode noise suppression)
- Frame transfer frequency 400kHz
- Peak Signal 1.4Me
- 97dB dynamic range

# TropOMI – Sentinel 5 precursor

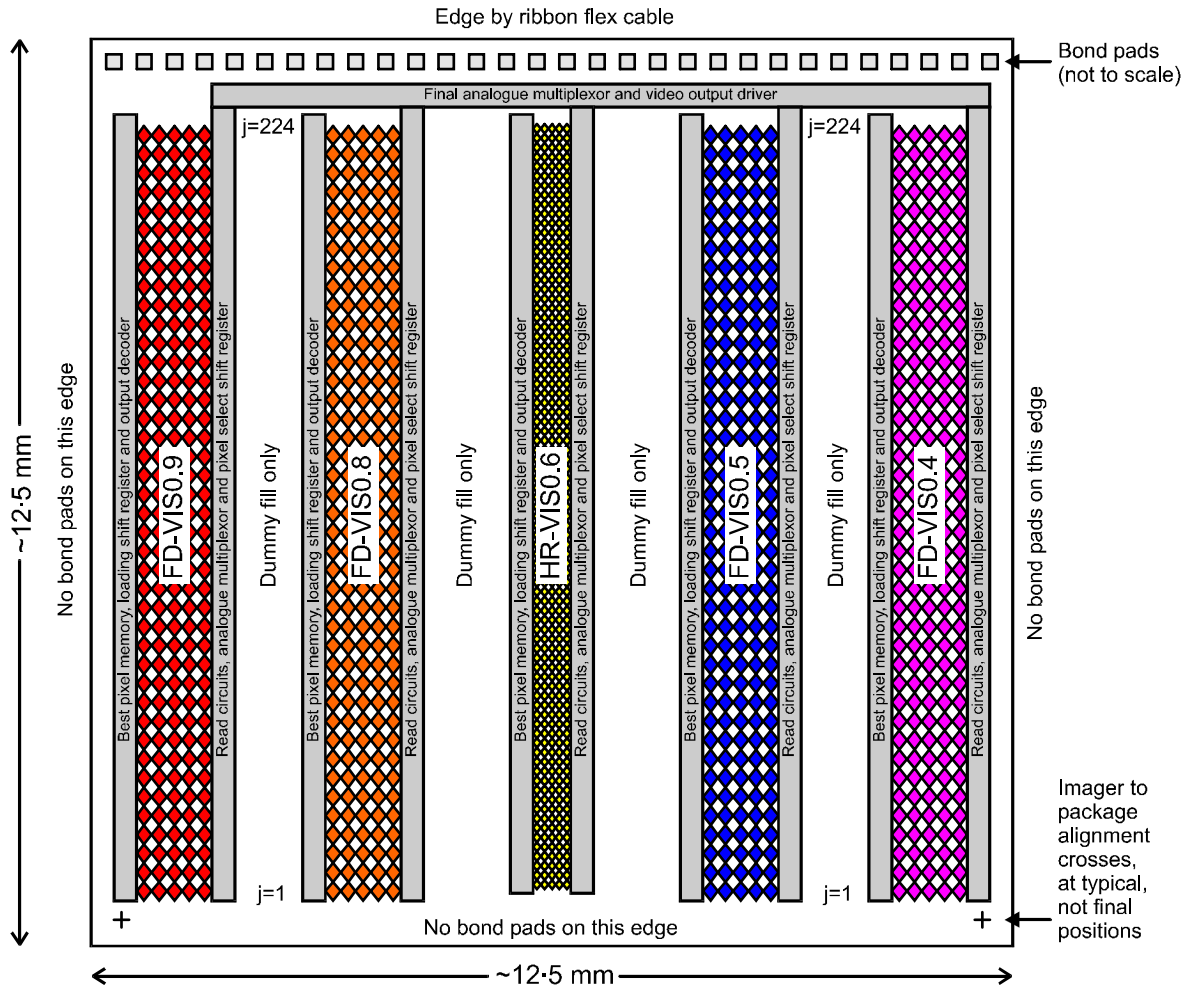
- TropOMI – Tropsheric Ozone Monitoring Instrument
- Aim to bridge the gap between Envisat / Aura and Sentinel 5 (2020)
- UV, VIS and NIR (40um thick epi) imagers
- CCD275
- 1024 x 1024 image area with 26 mm square pixels
- 2 phase image and store pixels with metalisation for fast line transfer
- 0.75µs per line
- 5MHz pixel frequency
- Peak signal >700ke with noise <50e
- Switchable gain amplifier





# MTG FCI sensor

- The format of the sensor is shown below with 5 channels of rhombus shaped pixels operating at different wavelengths



# MTG FCI Sensor 4T Pixel design

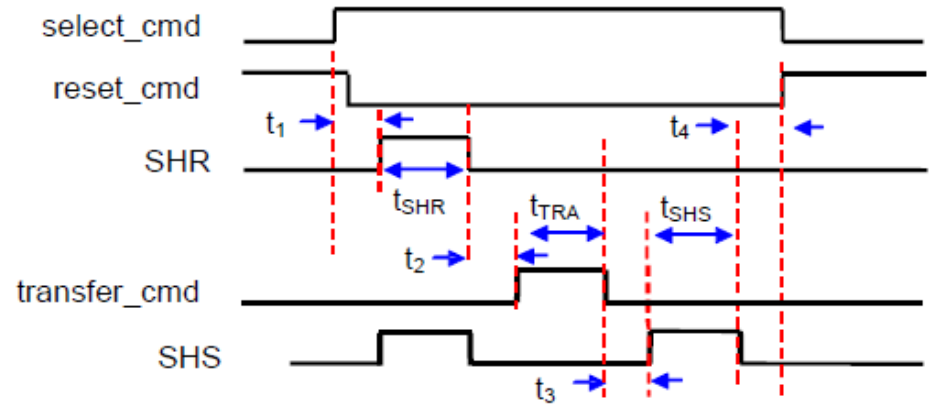
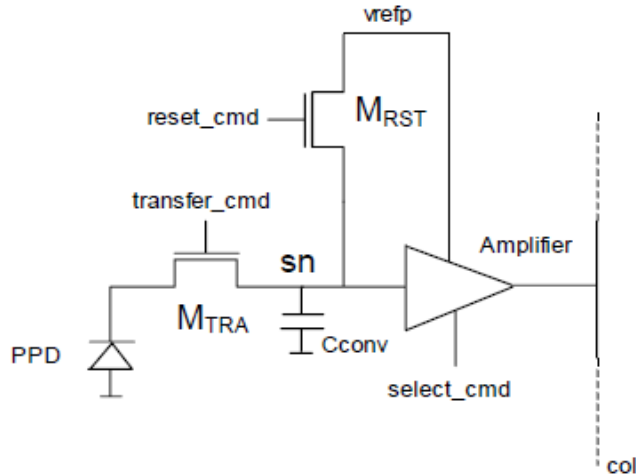
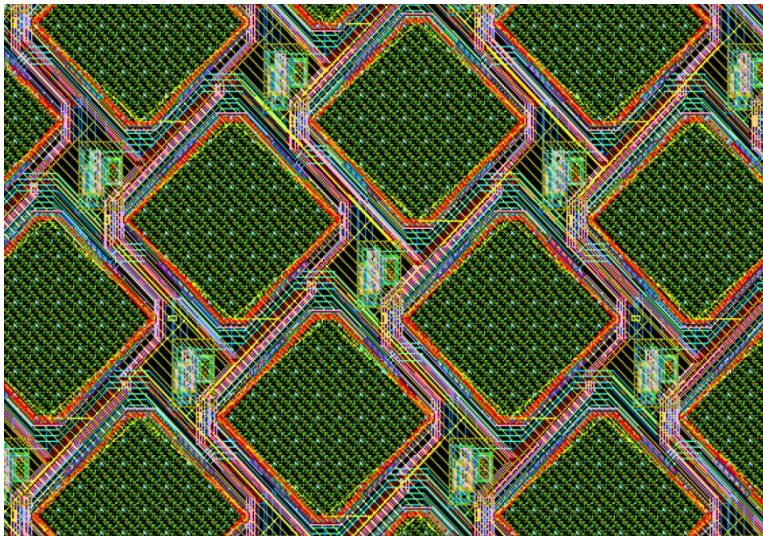


Figure 2: Pixel timing diagram.

Figure 1: Schematic representation of a 4T pixel with photodiode.



FD: ~ 80 um photodiode

HR: ~40um photodiode

The array is composed of Rhombus pixels for MTF considerations (effective pixel pitch is smaller than photodiode pitch)

Sensor is full radiation hard

Special implantation shape for optimized transfer

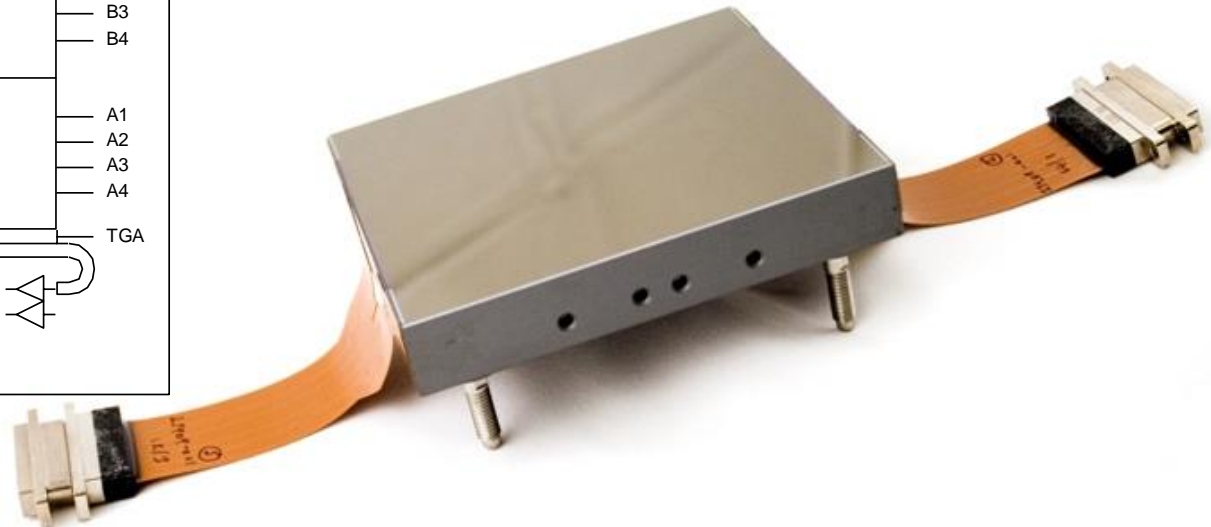
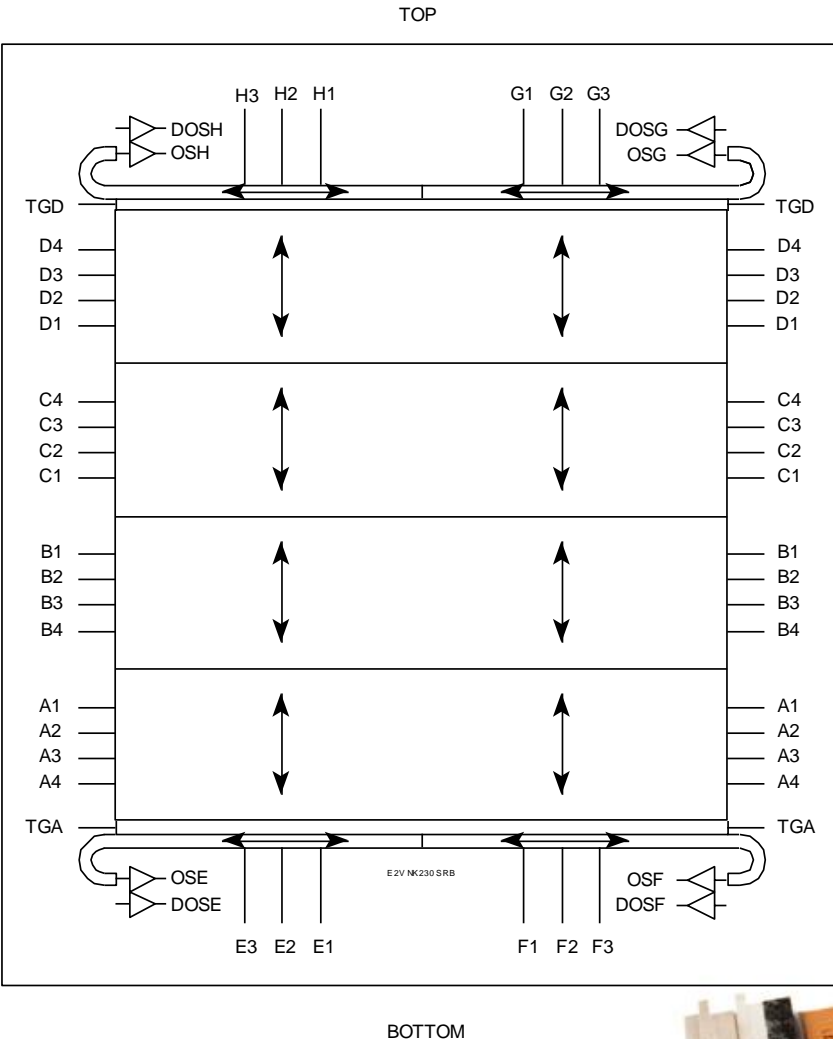
# Astronomy

Significant trends in Astronomy are:

- Push for increased Red Quantum Efficiency (HiRho)
- Larger area devices and Larger area Focal planes
- Some use of CMOS detectors

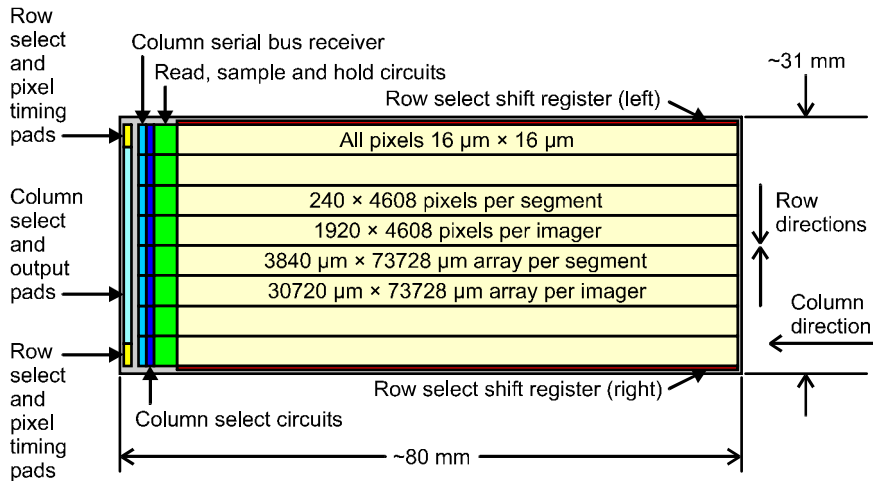
# Full wafer size CCD

- Available as both 6k x 6k with 15µm pixels and 4 outputs or 9k x 9k with 10µm pixels and 16 outputs.
- Both devices are 9cm square and fill a complete 6" silicon wafer



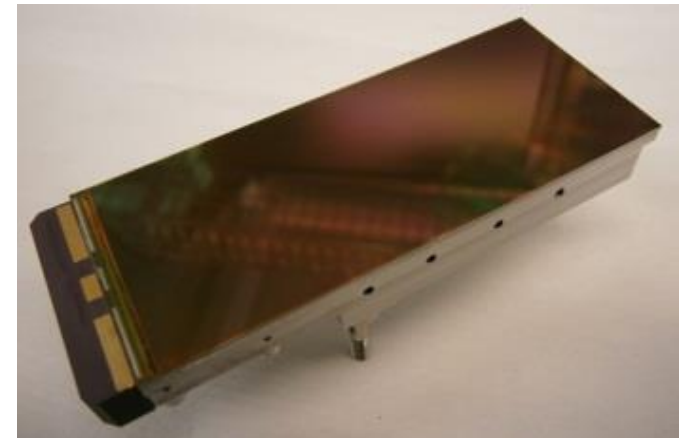
# CMOS imagers-1

## TAOS-II CIS113 sensor



Trans-Neptunian Object  
detection by occultation

**Sensor:** 1920 x 4608 16 μm square pixels.  
8 segments for parallel read-out  
Independent access of left and right sides  
Multiple ROI mode for 20 fps sampling rate  
Noise floor  $\sim 3e^-_{RMS}$  and low dark current.  
Backthinned for 90% QE  
Saturation signal (node)  $\sim 18 ke-$



# WaveFront Sensor (NGSD) for AO system on E-ELT

Used to measure atmospheric turbulence and drive correcting mirror

## Second samples early 2015

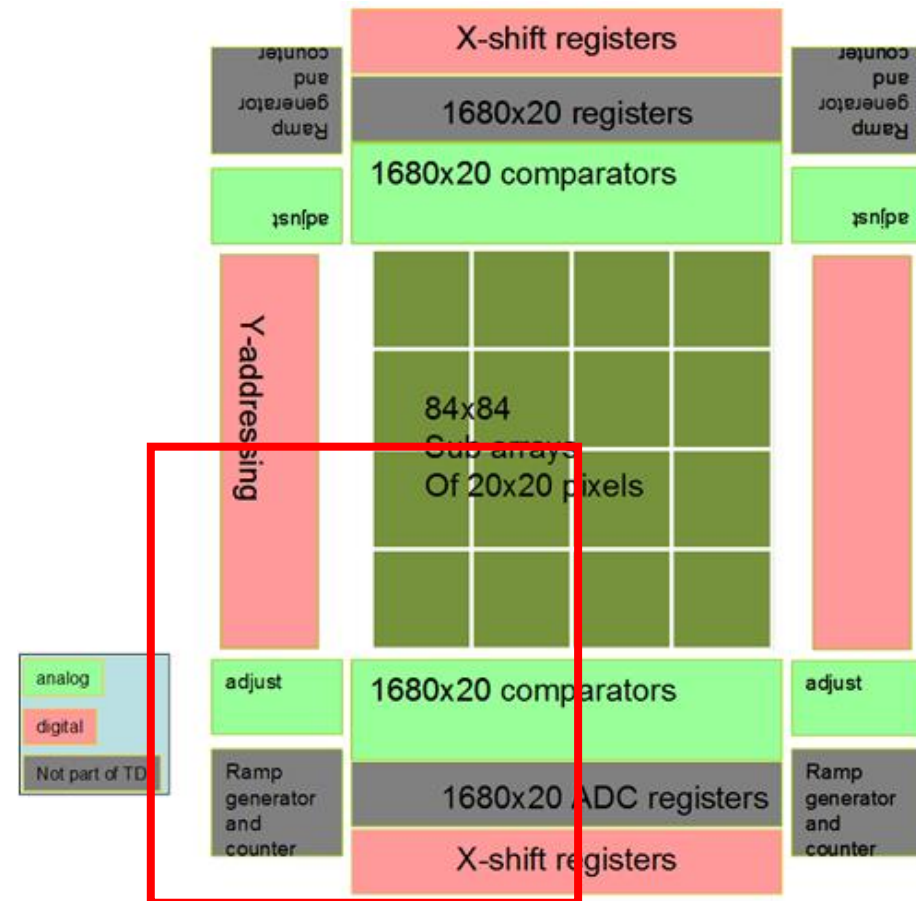
- Fully functional
- No data errors at 4.75 Gbps
- $< 4 e^-$  total noise measured
- Lag  $< 1 e^-$  at low levels
- Many performance requirements met

## But some problems found:

- Many hot pixels
- Interaction amongst the 17,600 ADC blocks
- Some digital to analogue feedback

Apart from solving these problems, customer also wants lower noise ( $< 3 e^-$ ) for use with laser guide stars.

This is expected to be possible

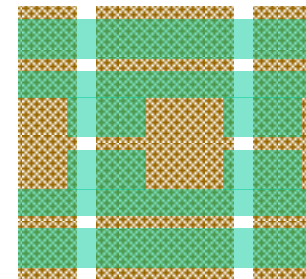




# X-Ray detection in space

e2v provide sensors for detection of soft X-Rays in space using three different technologies

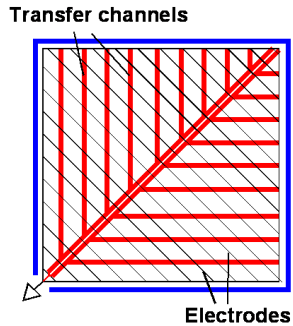
- 1 Backthinned sensors with no AR coating have been used for several solar observation projects including SDO, SXI (solar x-ray imager) and the X-Ray telescope on Hinode
- 2 Open electrode CCDs have a gap in the electrode allowing photons to get directly into the silicon. This structure is used on XMM



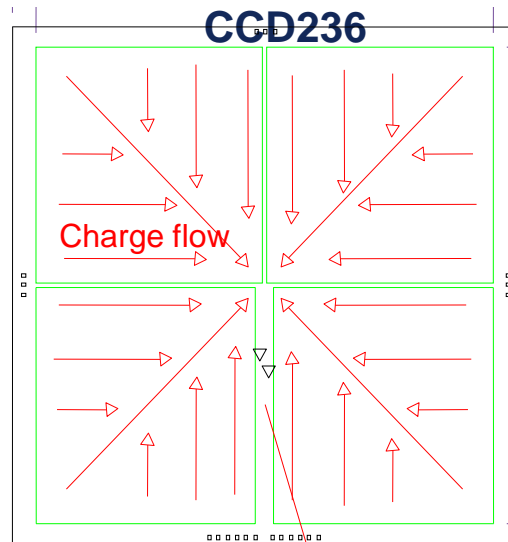
- 3 Swept charge CCDs are single pixel detectors that are used photodiode arrays – used on Chandryan and in HXMT

# X-Ray Spectroscopy

- HXMT uses CCD236 which is a larger version of the CCD54 used for lunar x-ray fluorescence measurements on Chandrayaan 1

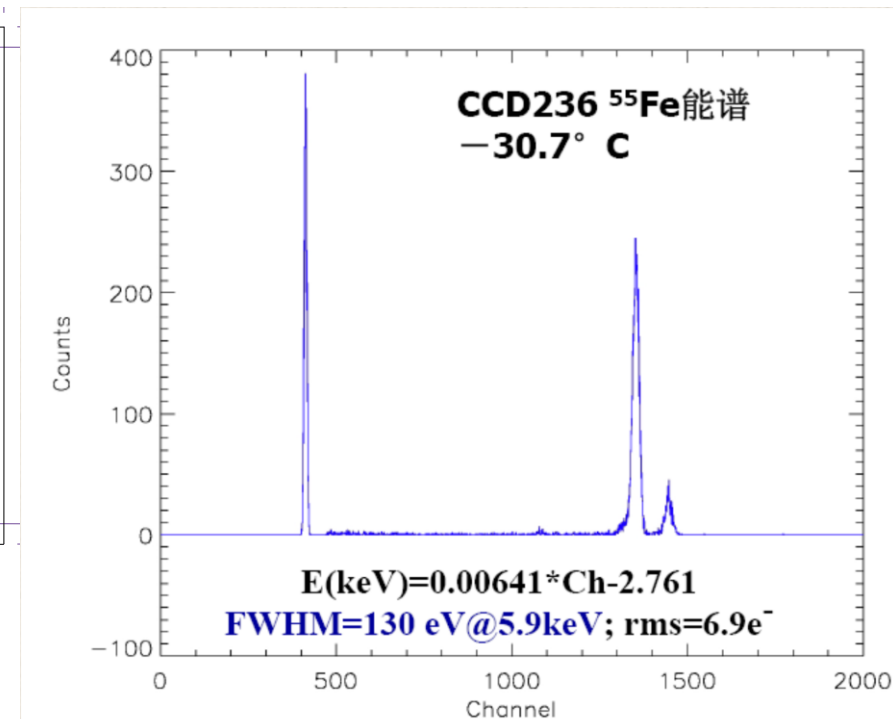


CCD54: 1cm<sup>2</sup> with charge output from one corner



Real & dummy outputs in gap

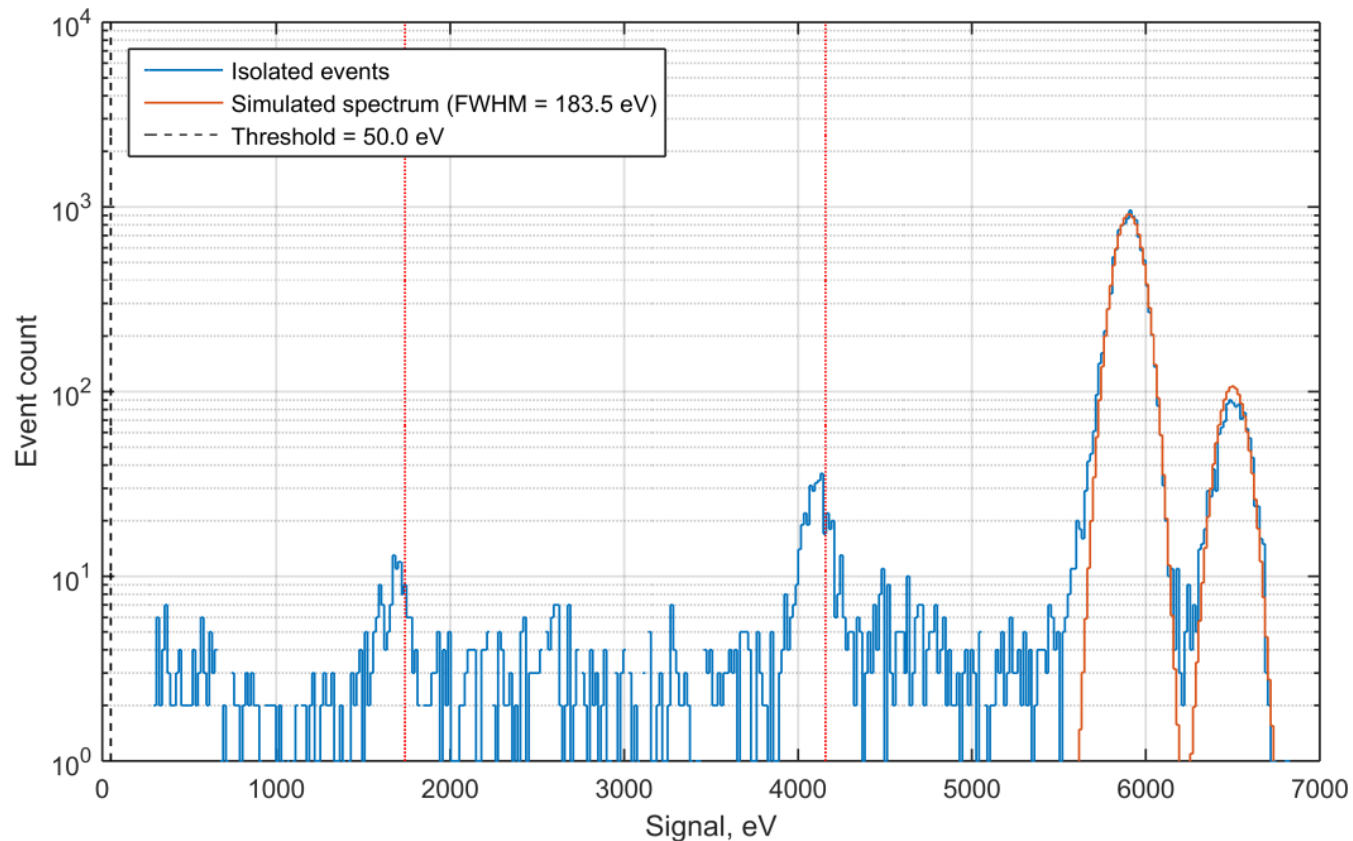
CCD236: 4cm<sup>2</sup> with charge output from the centre

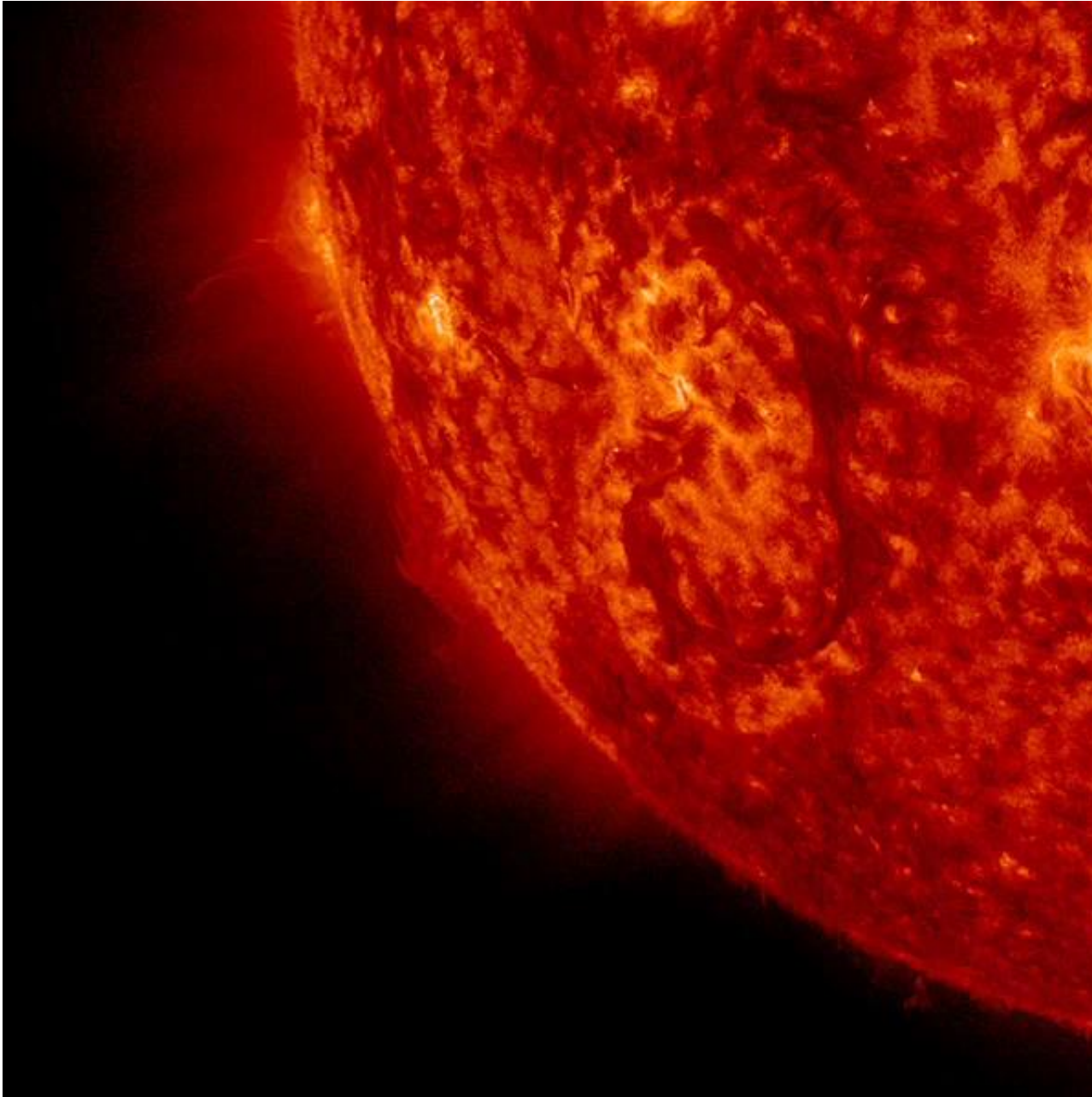




# X-ray spectroscopy with CMOS

- To date not as good as CCDs – latest results from the CEI (Open University) show good energy resolution from single events from Fe55





## SDO VUV images

# Topics

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- Examples of detector technology for space, science and astronomy:
- **Synchrotron radiation detectors**
- CCDs for XFELs
- CMOS sensors for synchrotron radiation detection

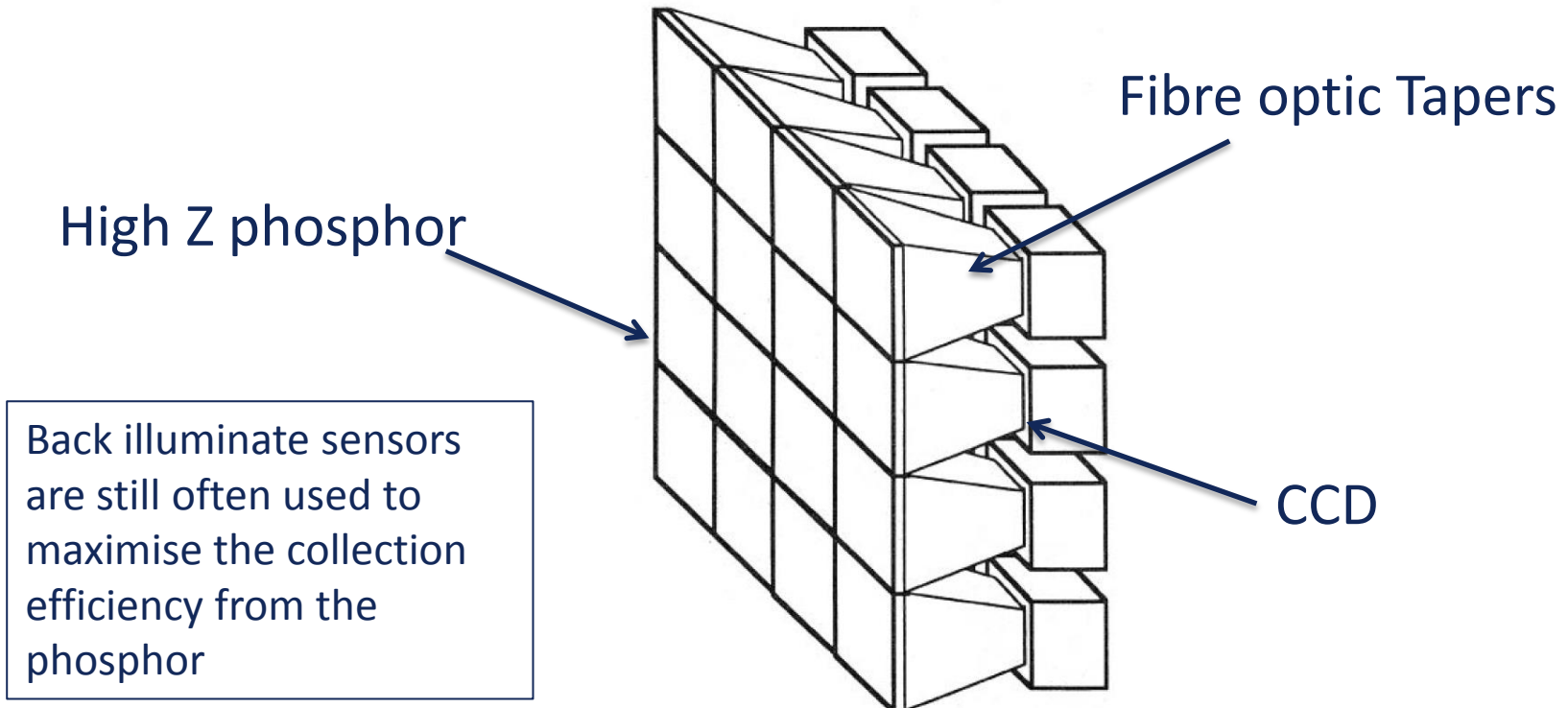
# Comparison to space detectors

Requirement	Space detectors	Soft X-ray detectors
Rad Hardness	Critical but only up to ~40kRads ionising dose often much less. But significant proton and heavy ion requirements	Only ionising radiation but up to extreme doses – 100s of MRads
Quantum efficiency	Critical for all applications sometimes into deep UV or Near IR so requires backthinning and sometimes thick silicon	<5keV 40µm thick silicon is OK >5keV requires up to 300µm thick silicon
Dynamic range	Critical for many astronomy and EO applications	As high as possible – especially high peak signal required ~4Me
Noise	Critical for astronomy application (~2e) less so for EO	Less critical than dynamic range
Frame rates	Generally not high apart from adaptive optics and photon counting for x-ray astronomy	At least 60Hz for XFELs
Pixel size	Typically 10-30µm	Currently 50 µm for medium x-ray Trending to 10-30µm for soft x-ray

# Synchrotron radiation detectors

## Indirect detection

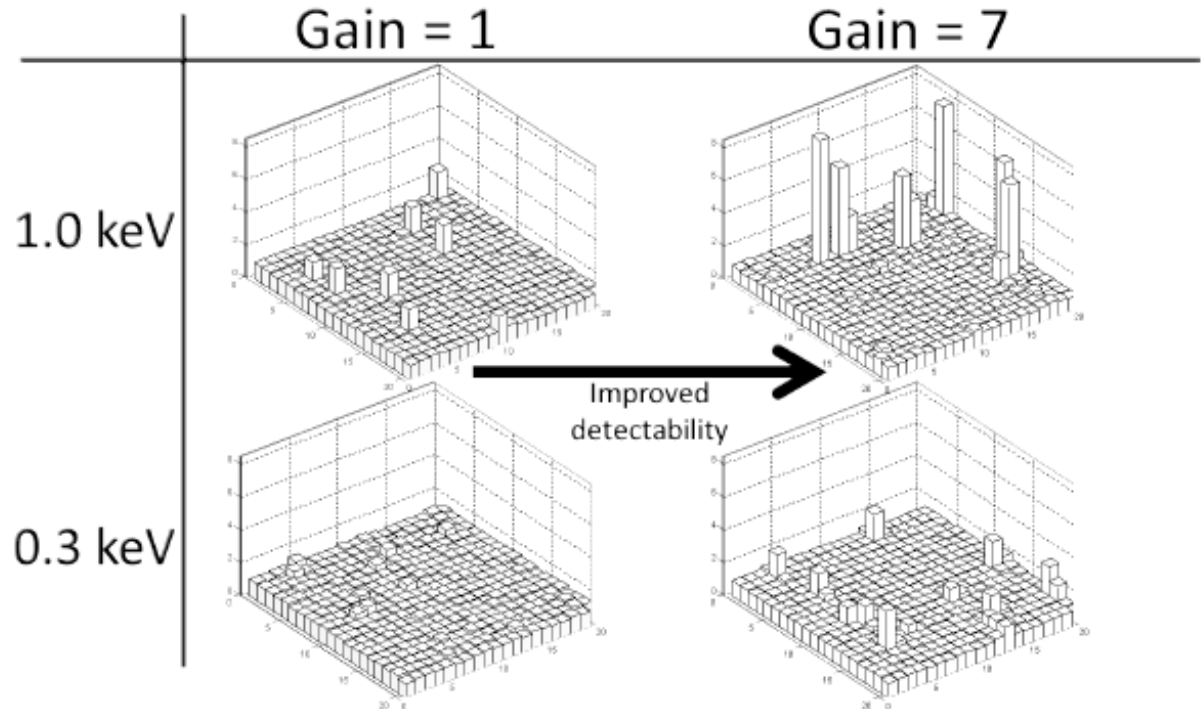
- Large area CCDs have been used on the back of fibre optic tapers for many years (eg M. Suzuki, M. Yamamoto, T. Kumasaka, K. Sato, H. Toyokawa, I. F. Aries, P. A. Jerram, D. Gullick and T. Ueki “A multiple-CCD X-ray detector and its basic characterization” *J. Synchrotron Rad.* (1999). 6, 6-18)
- These tend to use large area devices such as those used for Astronomy (CCD55-30 or CCD230-84)



# Direct Detection: Soft X-rays

## Electron multiplication in the charge domain

- The application of modest EM gain dramatically improves the detection of X-rays
- Here we see work done by the Open University demonstrating that a factor of x7 in gain significantly increases the signal to noise ratio



Ref: Electron-multiplying CCDs for future soft X-ray spectrometers

Tutt, J. H.; Holland, A. D.; Murray, N. J. ; Harriss, R. D.; Hall, D. J. and Soman, M. (2012).

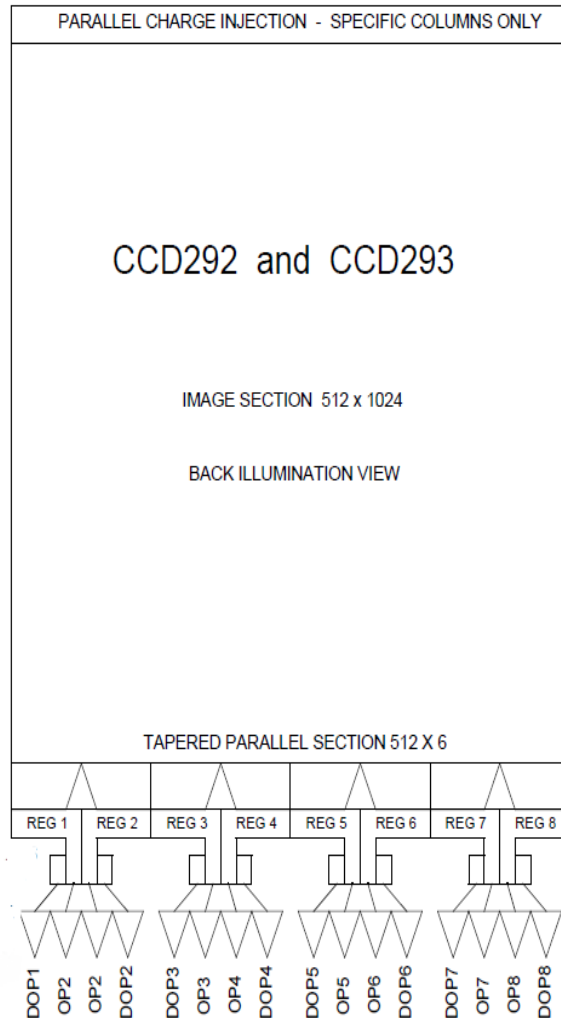
Journal of Instrumentation, 7(2) C02031.

## Topics

- **e2v Introduction**
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- **CCDs for XFELs**
- **CMOS sensors for synchrotron radiation detection**

# CCDs for XFELs

- The CCD 292 and CCD262 have been developed for Riken for x-ray detection in XFELs

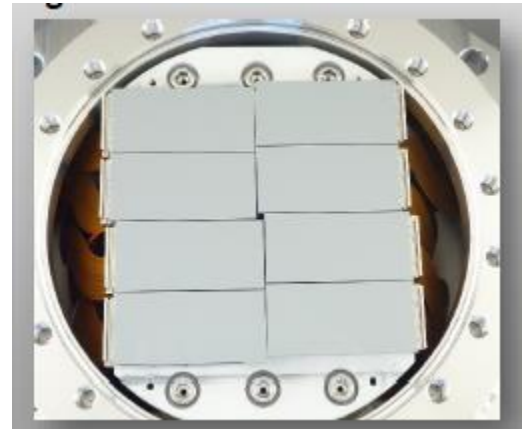
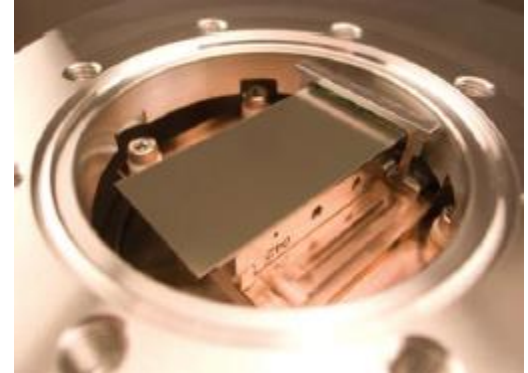


- CCD262 is standard deep depletion material front illuminated (40 $\mu$ m thick)
- CCD292 is HiRho back-illuminated (300 $\mu$ m thick)
- Pixel size is 50 $\mu$ m with 8 outputs with 2 phase image and store to provide a frame rate of up to 60Hz
- Up to 300 $\mu$ m thick to allow detection of soft x-rays up to 15keV



## XFEL Sensor portfolio

- CCD262-50, front illuminated deep depleted sensor capable of 60Hz frame rate operation.
- 512 x 1024 pixel format with 50  $\mu\text{m}$  x 50  $\mu\text{m}$  pixels
- Designed for assembly into a tiled array
- Peak X-ray QE of 90% at 4,000eV
- 80% QE at 6,000eV
- Peak signal 2.5 – 3.0 Me-
- System noise 100 – 250 e- rms @ 30Hz



*The sensor was developed with direction and funding from RIKEN. The images are from RIKEN and performance figures are as tested by RIKEN*

## XFEL Sensor portfolio

- The third sensor in the portfolio is the CCD293-50, a back illuminated sensor, which is a variant of the CCD292-50 with lower noise and lower peak signal.
- The three sensors compare as follows:

Description	CCD262-50	CCD292-50	CCD293-50
System noise [ph@6 keV]	0.06 – 0.15	0.12 -0.15	0.02 – 0.037
Peak signal [ph@6keV]	2500 - 3000	2100	970
Nominal QE [%@6 keV]	77	100	
Nominal QE [%@12keV]	19	73	
PSF* [µm r.m.s @12keV]	3.2 (150 phs)	9.4 (49 phs)	
	4.8 (910 phs)	14 (1030 phs)	
Comments	1 <sup>st</sup> generation	Better QE Broader PSF Application SFX	Lower noise Lower peak signal App. XQO, XAFS

# Systems for Photon Science

**RIKEN developed the systems to run single, dual, octal sensor cameras with the Multi-Port 262, 292 and 293 CCDs, MPCCDs.**

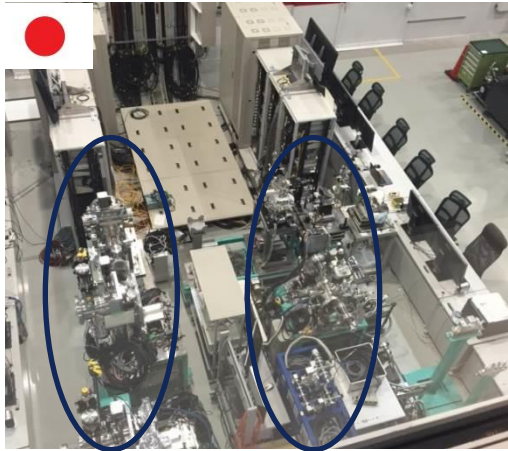
**e2v has lead a contract to deliver single sensor and dual sensor cameras to the Pohang Accelerator Laboratory (PAL) X-ray Free Electron Laser (XFEL)**

Pohang Accelerator Laboratory in South Korea are currently in the process of building a fourth generation XFEL and wish to use the MPCCD system. Majority of the work is conducted by Meisei wh

MPCCD sy

**Deliveries :**  
**2 single device systems : Aug/Sept 15**  
**3 Dual device systems Oct/Nov/Dec15**

In the case of the XFEL systems, re-use of RIKEN and Meisei's design minimised costs for PAL. As a thin-prime e2v still brings a number of benefits to the customer and future customer.



MPCCD dual System @ Spring 8



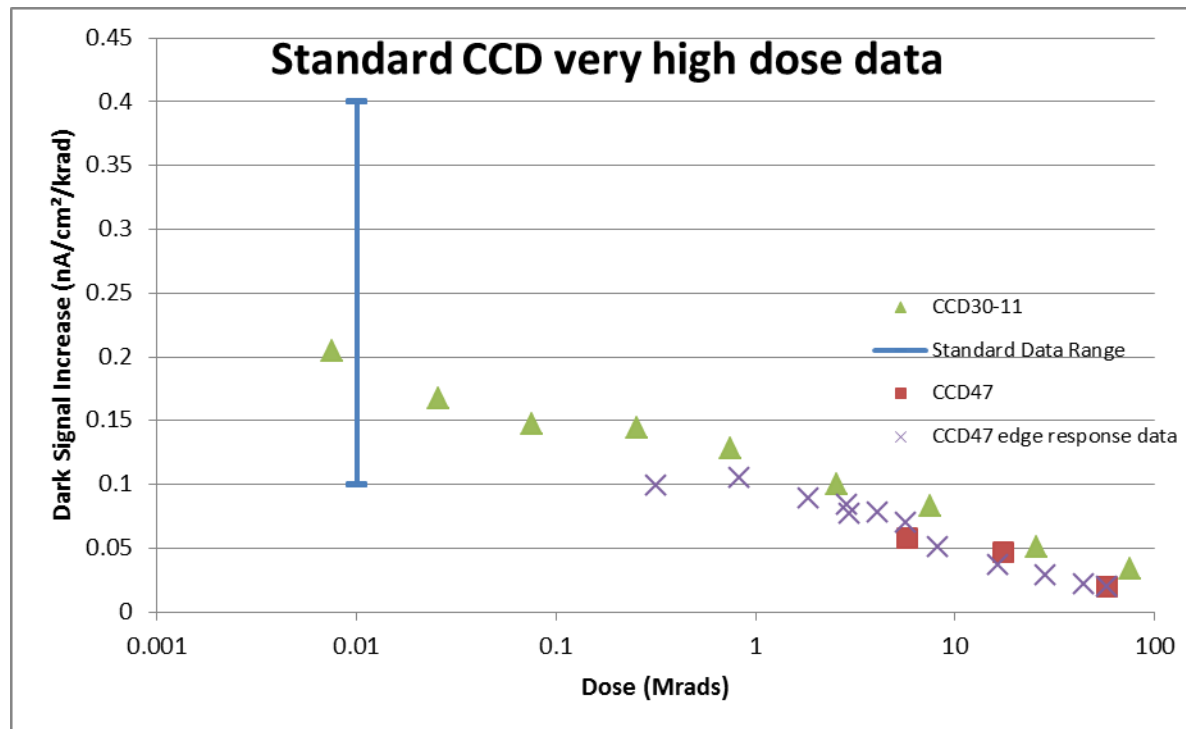
PAL Experiment Hall

Ionising radiation causes two effects on image sensors (CCDs and CMOS)

- A build up of positive charge causes a threshold shift that varies with oxide thickness (approximately  $\propto t_{\text{ox}}^2$ )
- The hydrogen anneal of the front surface is reversed giving an increase in dark signal ( $\propto t_{\text{ox}}$ )
- Our science CCDs use a thick gate oxide and so both of the effects were a major concern, however it was found working with Riken and XCAM that both of these effects saturate
- For example threshold shift at low doses is  $\sim 0.2\text{V/kRad}$  so after the 60MRad dose reread by Riken this would have given 12,000V threshold shift!

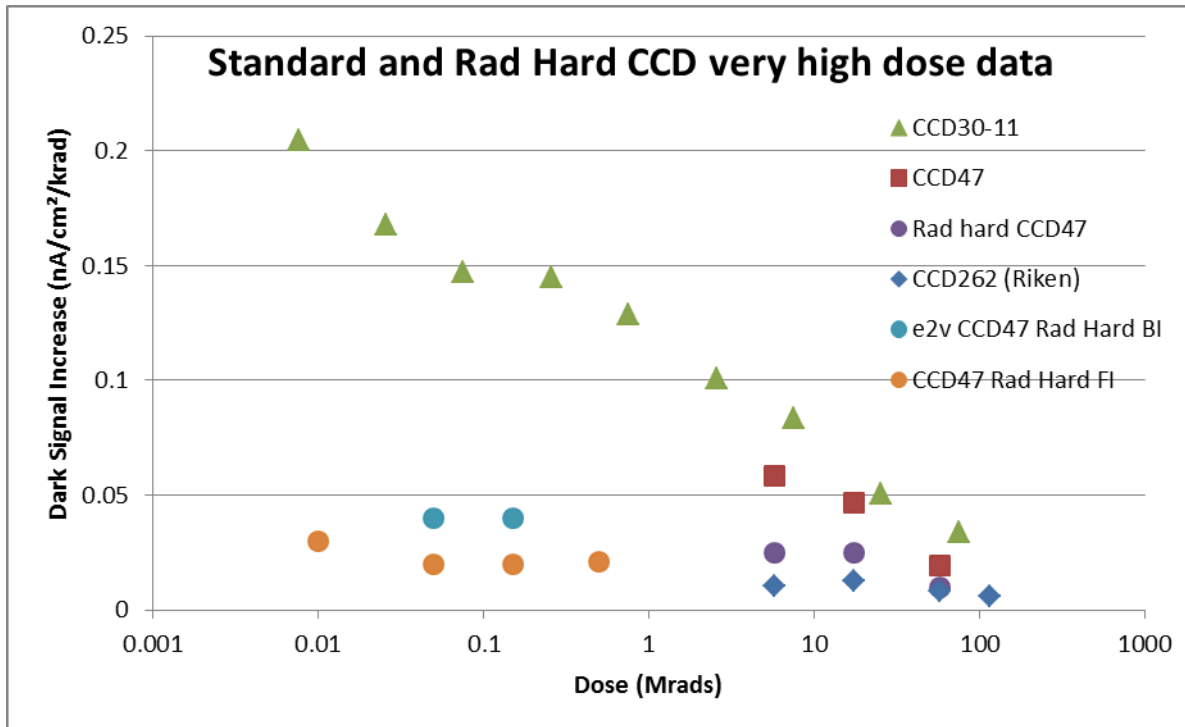
# Rad hard Dark signal

- Adding the scanned beam data to the rad had and standard silicon gives the results shown on the next slides



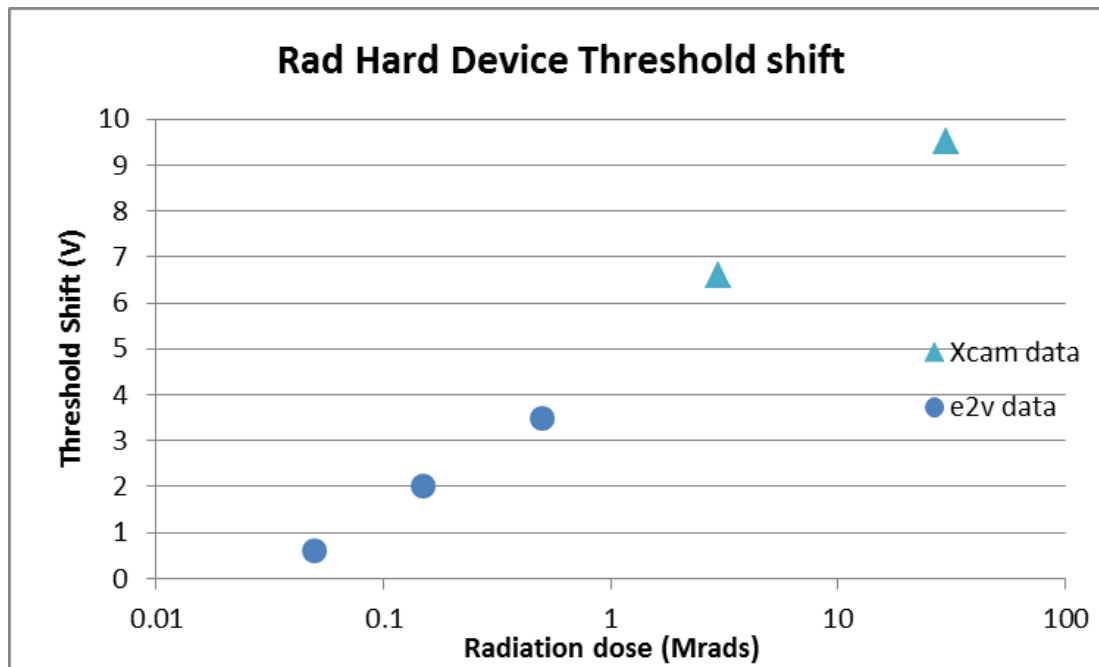
# Dark Signal Variation

- The plot below includes data from Radiation Hard CCDs.
  - For the rad hard device that dark signal increase is significantly lower
  - Also varies much less with dose



# Threshold shift

- Although plotted on a log-lin graph the data looks remarkably consistent – it would be good to have a physical explanation for this?
- Above ~50krads there is an increased of threshold shift of 1V every time the radiation dose doubles



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# CMOS requirements

## **Good radiation hardness**

A significant advantage of standard commercial CMOS processes is that the very thin gates inherently give a good degree of radiation hardness

## **High dynamic range**

Generally worse for CMOS than for CCDs but there are techniques available to improve dynamic range that are under investigation at e2v

## **Very high frame rate**

A major advantage of CMOS over the existing detectors and a strong reason to move to CMOS technology

## **Thick silicon for good QE**

This represents the major challenge for CMOS HiRho structures are more complex and it is also more of a challenge to get foundries to carry our non-standard processes. However the principles are the same as for CCDs in that a large negative voltage needs to be applied to the back surface – or use hybrids

## **Backthinning**

**Large area coverage** – large devices 3 side buttable device + packaging. In principle easier than for CCDs